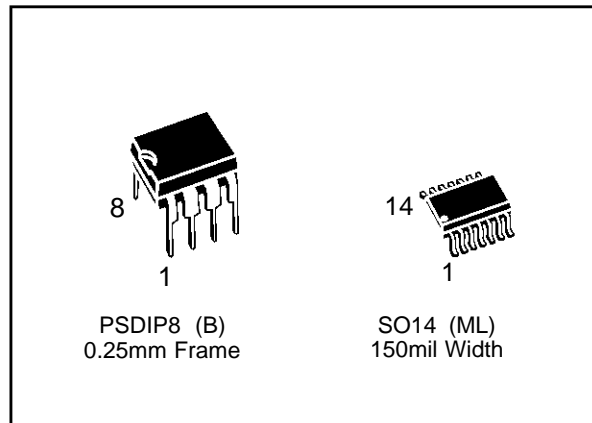


SERIAL MICROWIRE BUS 4K (256 x 16) EEPROM

DATA BRIEFING

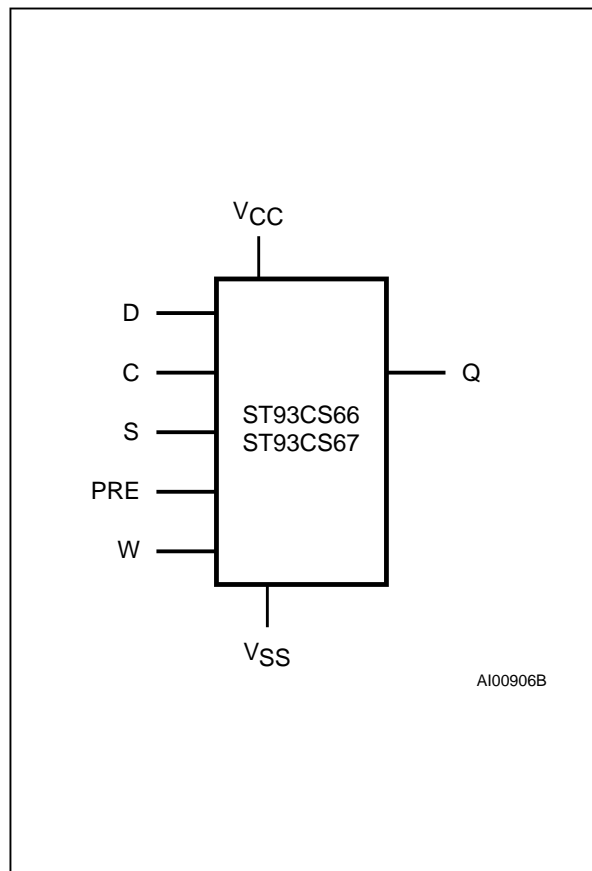
- 1 MILLION ERASE/WRITE CYCLES, with 40 YEARS DATA RETENTION
- SELF-TIMED PROGRAMMING CYCLE with AUTO-ERASE
- READY/BUSY SIGNAL DURING PROGRAMMING
- SINGLE SUPPLY VOLTAGE
 - 3V to 5.5V for the ST93CS66
 - 2.5V to 5.5V for the ST93CS67
- USER DEFINED WRITE PROTECTED AREA
- PAGE WRITE MODE (4 WORDS)
- SEQUENTIAL READ OPERATION
- 5ms TYPICAL PROGRAMMING TIME



DESCRIPTION

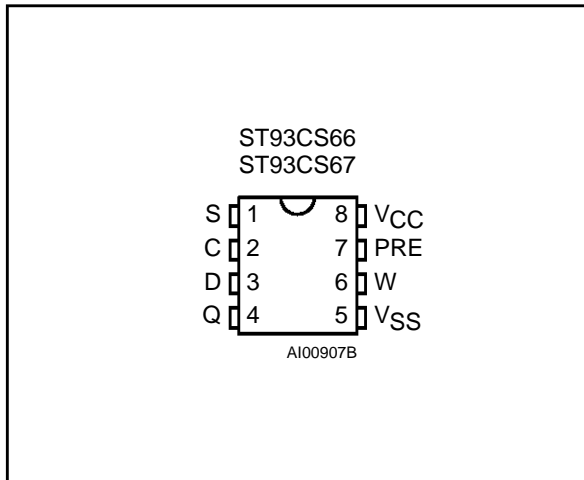
The ST93CS66 and ST93CS67 are 4K bit Electrically Erasable Programmable Memory (EEPROM) fabricated with SGS-THOMSON's High Endurance Single Polysilicon CMOS technology. The memory is accessed through a serial input D and output Q. The 4K bit memory is organized as 256 x 16 bit words. The memory is accessed by a set of instructions which include Read, Write, Page Write, Write All and instructions used to set the memory protection. A Read instruction loads the address of the first word to be read into an internal address pointer.

Logic Diagram



ST93CS66, ST93CS67

DIP Pin Connections



Signal Names

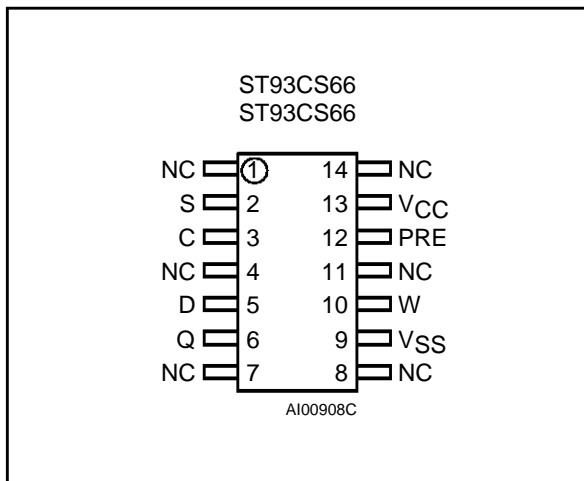
S	Chip Select Input
D	Serial Data Input
Q	Serial Data Output
C	Serial Clock
PRE	Protect Enable
W	Write Enable
V _{CC}	Supply Voltage
V _{SS}	Ground

Ordering Information Scheme

For a list of available options refer to the current Memory Shortform catalogue.

For further information on any aspect of this device, please contact the SGS-THOMSON Sales Office nearest to you.

SO Pin Connections



Warning: NC = Not Connected.

Example: ST93CS66 M 1 013TR

Operating Voltage	
66	3V to 5.5V
67	2.5V to 5.5V
Package	
B	PSDIP8 0.4mm Frame
M	SO14 150mil Width
Temp. Range	
1	0 to 70 °C
6	-40 to 85 °C
3	-40 to 125 °C
Option	
013TR	Tape & Reel Packing